

ABSTRACT**Method For Producing A Single-Crystal Film Of AlN Material And
Substrate For The Epitaxial Growth Of A Single-Crystal Film Of AlN
Material**

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A process for producing a monocrystalline layer of AlN material comprising the transfer of a monocrystalline seed layer of SiC-6H material to a carrier substrate of silicon material followed by epitaxial growth of the monocrystalline layer of AlN material.

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Figure 2